Continental Device India Limited

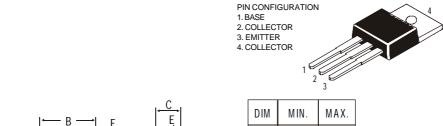


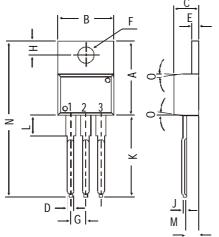
TO-220 Plastic Package

CSB507, CSD313

CSB507 PNP PLASTIC POWER TRANSISTOR CSD313 NPN PLASTIC POWER TRANSISTOR

Low frequency Power Amplifier Applications





	DIM	MIN.	MAX.
All UIIIIISIOIIS III IIIII.	А	14.42	16.51
	В	9.63	10.67
	С	3.56	4.83
	D		0.90
	E	1.15	1.40
	F	3.75	3.88
	G	2.29	2.79
	Н	2.54	3.43
	J		0.56
	K	12.70	14.73
	L	2.80	4.07
	М	2.03	2.92
	N		31.24
Ē	0	DEG 7	

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	60 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	60 V
Collector current	I_C	max.	3.0 A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	30 W
Junction temperature	T_{j}	max.	150 °C
Collector-emitter saturation voltage	v		
$I_C = 2A$; $I_B = 0.2A$	V_{CEsat}	max.	1.0 V
D.C. current gain			
$I_C = 1A$; $V_{CE} = 2V$	$h_{\!F\!E}$	min	40
		max.	320

RATINGS (at T_A =25°C unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CBO}	max.	60 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	60 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V

Collector current	I_C	max.	3.0 A
Collector current (Peak value)	I_{CM}	max.	8.0 A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	30 W
Junction temperature	T_j	max.	150 ℃
Storage temperature	T_{stg}	-65 to +150 ℃	
THERMAL CHARACTERISTICS			
From junction to case	$R_{th j-c}$	=	4.17 CW
Tront function to case	rin j-c	_	4.17 CW
CHARACTERISTICS			
$T_{amb} = 25^{\circ}C$ unless otherwise specified			
Collector cutoff current			
$I_E = 0$; $V_{CB} = 20V$	I_{CBO}	max.	0.1 mA
$I_B = 0; \ V_{CE} = 60V$	I_{CEO}	max.	5.0 mA
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 4V$	I_{EBO}	max.	1.0 mA
Breakdown voltages			
$I_C = 1 \text{ mA}; I_B = 0$	V_{CFO}	min.	60 V
$I_C = 1 \text{ mA}; I_E = 0$	V_{CBO}	min.	60 V
$I_E = 1 \text{ mA}; I_C = 0$	V_{EBO}	min.	5.0 V
Saturation voltage	LDO		
$I_C = 2 A$; $I_B = 0.2 A$	V_{CEsat}^*	max.	1.0 V
Base emitter on voltage	CESal	*******	1.0 ,
$I_C = 1A; V_{CE} = 2V$	$V_{BE(on)}^*$	max.	1.5 V
D.C. current gain	V BE(on)	max.	1.0 V
8	h*	min.	40
$I_C = 0.1A; \ V_{CE} = 2V$	h_{FE}^*	111111.	40
$I_C = 1A$; $V_{CF} = 2V^{**}$	$h_{\!F\!E}^*$	min.	40
IC III, VCE AV	-TL	max.	320
Transition frequency		mun,	020
$I_C = 500 \text{ mA}; V_{CE} = 5V$	f_T	tvn	8 MHz
IC = 300 HPA, VCE = 3V	11	typ.	o witz

^{*} Pulse test: pulse width \leq 300 μ s; duty cycle \leq 2.0%.

^{**} h_{FE} classification: C: 40-80 D: 60-120 E: 100-200 F: 160-320

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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